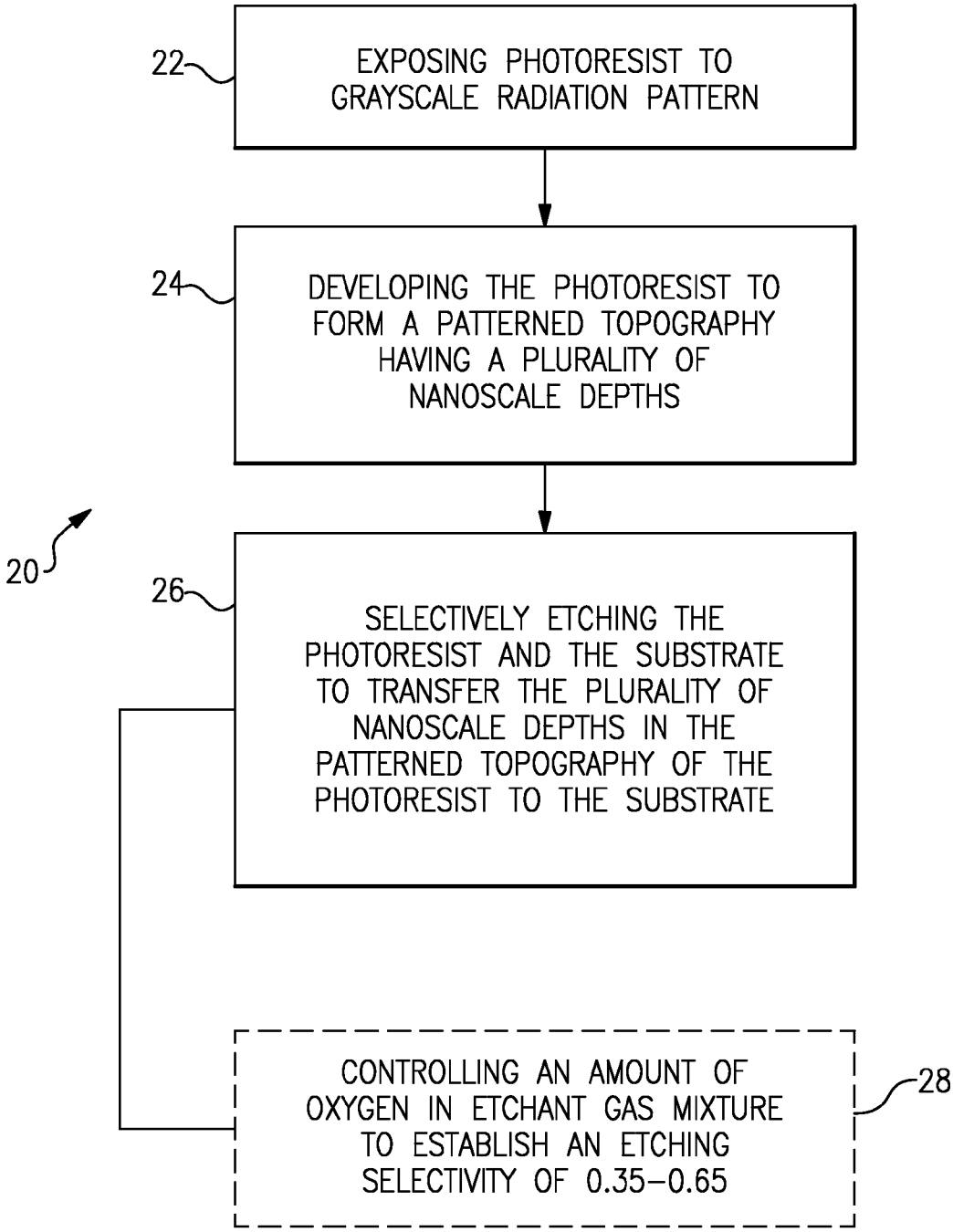
22
EXPOSING PHOTORESIST TO GRAYSCALE RADIATION PATTERN
24
DEVELOPING THE PHOTORESIST TO FORM A PATTERNED TOPOGRAPHY HAVING A PLURALITY OF NANOSCALE DEPTHS
20
26
SELECTIVELY ETCHING THE PHOTORESIST AND THE SUBSTRATE TO TRANSFER THE PLURALITY OF NANOSCALE DEPTHS IN THE PATTERNED TOPOGRAPHY OF THE PHOTORESIST TO THE SUBSTRATE
CONTROLLING AN AMOUNT OF OXYGEN IN ETCHANT GAS MIXTURE TO ESTABLISH AN ETCHING SELECTIVITY OF 0.35–0.65
28

FIG.1